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CCS H 80



**NATIONAL STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

GB/T 24574-2009

**Test methods for photoluminescence analysis of single crystal
silicon for III-V impurities**

硅单晶中III-V族杂质的光致发光测试方法
(English Translation)

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What this standard covers

This standard specifies the silicon single product in ??-?? photoluminescence testing methods ethnic impurities. This standard applies to the determination of low dislocation single crystal silicon impurity conductivity of boron and phosphorus content simultaneously. This standard is used to detect a single product silicon content of 1×10^{11} at cm^{-3} $\sim 5 \times 10^{15}$ at cm^{-3} for a variety of electrically active impurity elements.

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